

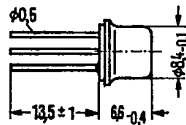
NPN Silicon Planar Transistors

**BSX 45
BSX 46
BSX 47**

SIEMENS AKTIENGESELLSCHAFT D

BSX 45, BSX 46, and BSX 47 are epitaxial NPN silicon planar transistors in TO 39 case (5 C 3 DIN 41873). Their collectors are electrically connected to their cases. The transistors are particularly suitable for AF amplifiers and AF switching applications up to 1 A.

Type	Ordering code
BSX 45 ¹⁾	Q60218-X45
BSX 45-6	Q60218-X45-V6
BSX 45-10	Q60218-X45-V10
BSX 45-16	Q60218-X45-V16
BSX 46 ¹⁾	Q60218-X46
BSX 46-6	Q60218-X46-V6
BSX 46-10	Q60218-X46-V10
BSX 46-16	Q60218-X46-V16
BSX 47 ¹⁾	Q60218-X47
BSX 47-6	Q60218-X47-V6
BSX 47-10	Q60218-X47-V10



Approx. weight 1.5 g



Dimensions in mm

Maximum ratings

		BSX 45	BSX 46	BSX 47	
Collector-emitter voltage	V_{CEO}	40	60	80	V
Collector-emitter voltage	V_{CES}	80	100	120	V
Emitter-base voltage	V_{EBO}	7	7	7	V
Collector current	I_C	1	1	1	A
Base current	I_B	0.2	0.2	0.2	A
Junction temperature	T_j	200	200	200	°C
Storage temperature range	T_{stg}		-65 to +200		°C
Total power dissipation ($T_{case} \leq 25^\circ C$)	P_{tot}	5	5	5	W

Thermal resistance

Junction to ambient air	R_{thJA}	≤ 200	≤ 200	≤ 200	K/W
Junction to case	R_{thJC}	≤ 35	≤ 35	≤ 35	K/W

Static characteristics ($T_{amb} = 25^\circ C$)

Transistors BSX 45, BSX 46, and BSX 47 are grouped according to their DC current gain h_{FE} at $I_C = 100$ mA and $V_{CE} = 1$ V. The different groups are marked by figures of the DIN-R 5 standard series.

Type	BSX 45 BSX 46 BSX 47	BSX 45 BSX 46 BSX 47	BSX 45 BSX 46 -	BSX 45 BSX 46 BSX 47
h_{FE} group	6	10	16	
I_C mA	h_{FE} I_C/I_B	h_{FE} I_C/I_B	h_{FE} I_C/I_B	V_{BE} V
0.1	28 (> 10)	40 (> 15)	90 (> 25)	-
100	63 (40 to 100)	100 (63 to 160)	160 (100 to 250)	< 1
500	25 (> 15)	40 (> 25)	60 (> 35)	0.75 to 1.5
1000	15	20	30	1.3 (< 2)

1) In case of orders without an exact indication of the current amplification wanted, a transistor will be delivered of that current amplification group available at stock.

SIEMENS AKTIENGESELLSCHAFT

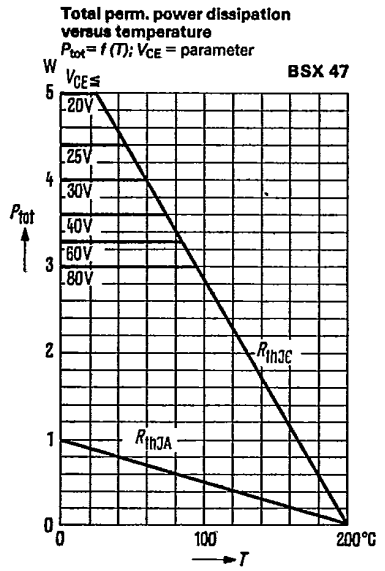
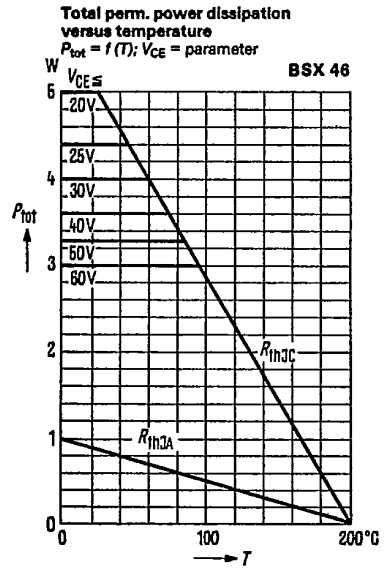
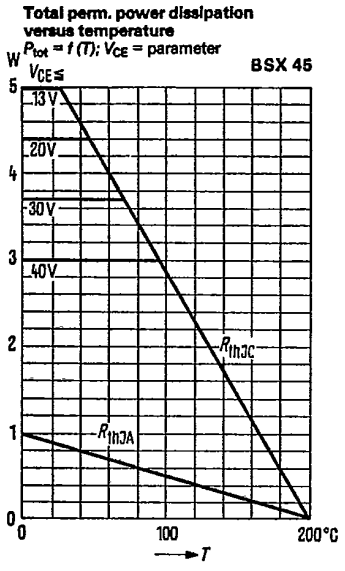
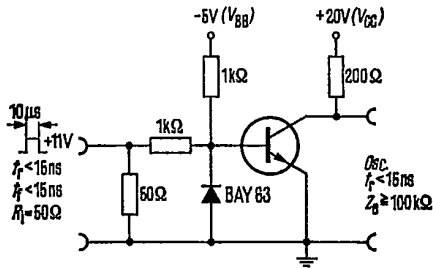
Static characteristics ($T_{amb} = 25^{\circ}\text{C}$)		BSX 45	BSX 46	BSX 47	
Collector-emitter saturation voltage ($I_C = 1\text{ A}; h_{FE} = 10$)	V_{CEsat}	0.7 (<1)	0.7 (<1)	-	V
Collector-emitter saturation voltage ($I_C = 0.5\text{ A}; h_{FE} = 20$)	V_{CEsat}	-	-	0.5 (<0.9)	V
Collector cutoff current ($V_{CES} = 60\text{ V}$)	I_{CES}	1 (<30)	1 (<30)	-	nA
Collector cutoff current ($V_{CES} = 60\text{ V}; T_{amb} = 150^{\circ}\text{C}$)	I_{CES}	1 (<10)	1 (<10)	-	μA
Collector cutoff current ($V_{CES} = 80\text{ V}$)	I_{CES}	-	-	<30	nA
Collector cutoff current ($V_{CES} = 80\text{ V}; T_{amb} = 150^{\circ}\text{C}$)	I_{CES}	-	-	<10	μA
Collector cutoff current ($V_{CE} = 60\text{ V}; V_{BE} = 0.2\text{ V}; T_{amb} = 100^{\circ}\text{C}$)	I_{CEX}	<50	<50	-	μA
Collector cutoff current ($V_{CE} = 80\text{ V}; V_{BE} = 0.2\text{ V}; T_{amb} = 100^{\circ}\text{C}$)	I_{CEX}	-	-	<50	μA
Emitter cutoff current ($V_{EBO} = 5\text{ V}$)	I_{EBO}	<10	<10	<10	nA
Collector-emitter breakdown voltage ($I_{CE} = 50\text{ mA};$ pulse length = 200 $\mu\text{s};$ duty cycle 1%)	$V_{(BR)CEO}$	>40	>60	>80	V
Collector-emitter breakdown voltage ($I_{CES} = 100\text{ }\mu\text{A}$)	$V_{(BR)CES}$	>80	>100	>120	V
Emitter-base breakdown voltage ($I_{EBO} = 100\text{ }\mu\text{A}$)	$V_{(BR)EBO}$	>7	>7	>7	V

Dynamic characteristics ($T_{amb} = 25^{\circ}\text{C}$)

Transition frequency ($I_C = 50\text{ mA}; V_{CE} = 10\text{ V}; f = 20\text{ MHz}$)	f_T	>50	>50	>50	MHz
Collector-base capacitance ($V_{CBO} = 10\text{ V}; f = 1\text{ MHz}$)	C_{CBO}	<25	<20	<15	pF
Emitter-base capacitance ($V_{EBO} = 0.5\text{ V}; f = 1\text{ MHz}$)	C_{EBO}	<80	<80	<80	pF
Noise figure ($I_C = 100\text{ }\mu\text{A}; V_{CE} = 10\text{ V}; f = 1\text{ kHz}; \Delta f = 200\text{ Hz}; R_g = 1\text{ k}\Omega$)	NF	3.5	3.5	3.5	dB
Switching times $I_C = 100\text{ mA}; I_{B1} \text{ approx. } -I_{B2} \text{ approx. } 5\text{ mA}$	t_{on} t_{off}	<200 <850	<200 <850	<200 <850	ns ns

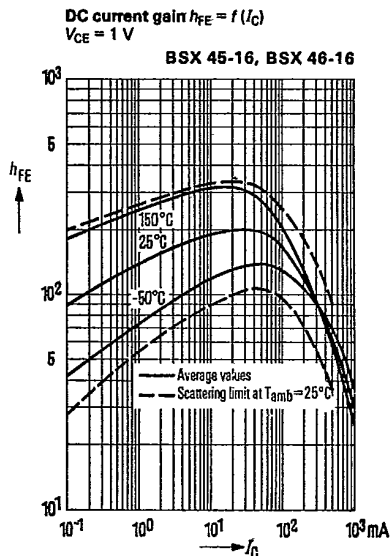
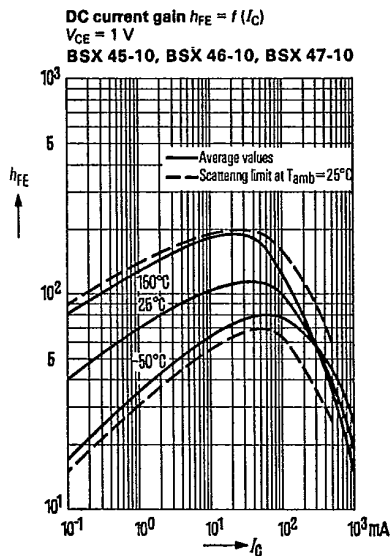
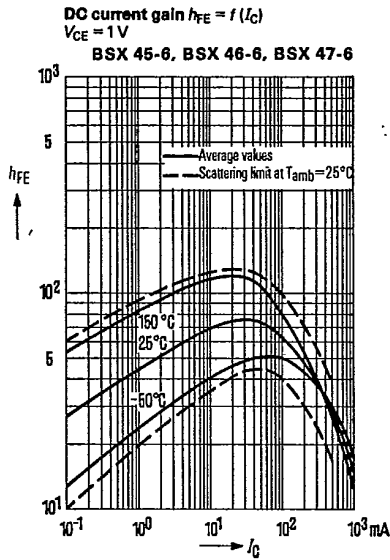
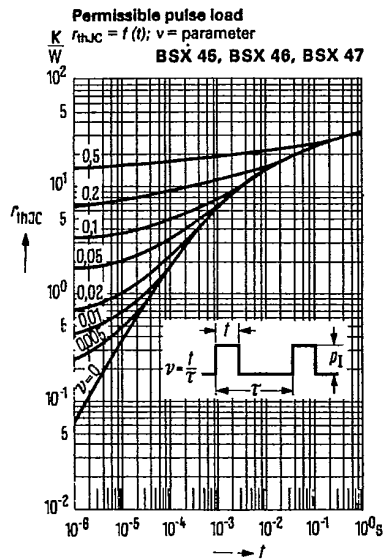
- SIEMENS AKTIENGESELLSCHAFT

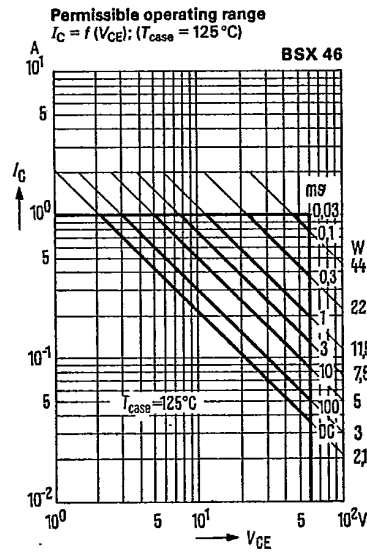
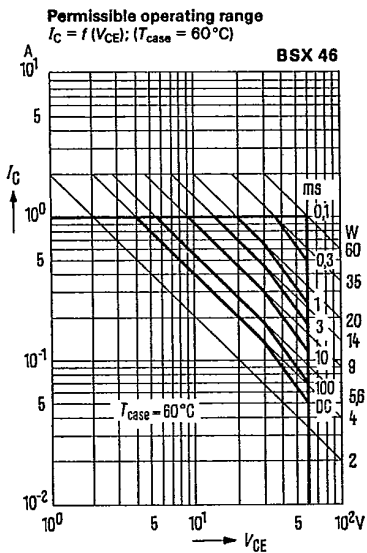
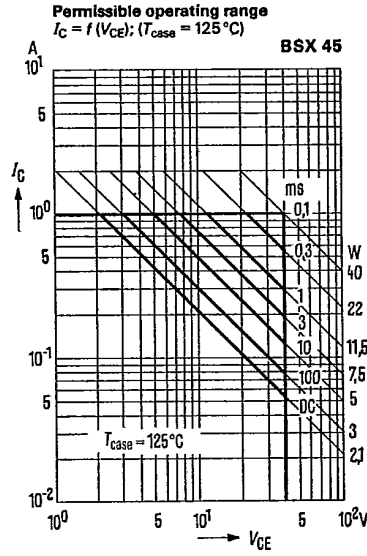
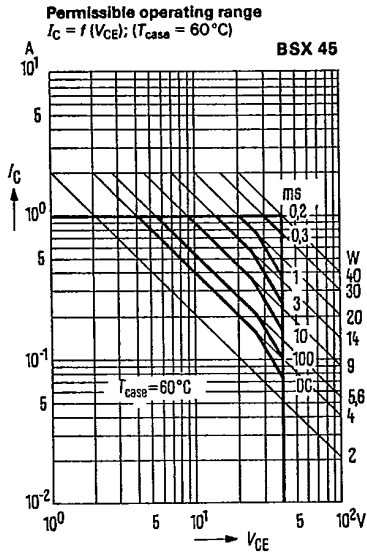
Test circuit for switching times



SIEMENS AKTIENGESELLSCHAFT

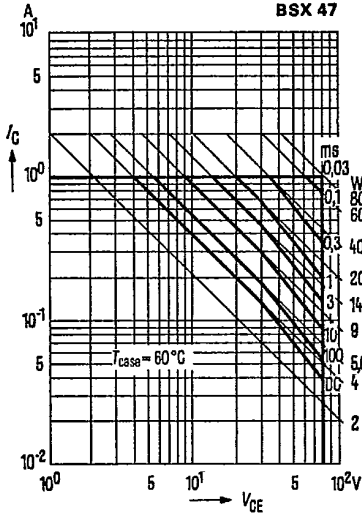
BSX 45
BSX 46
BSX 47



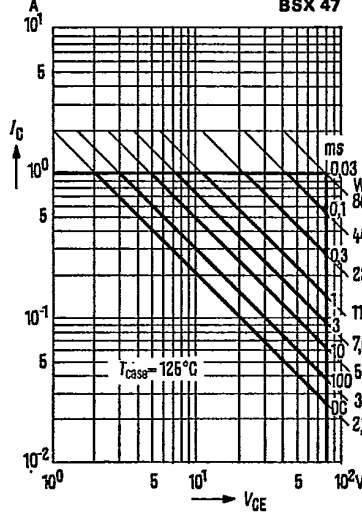


The permissible operating ranges apply to single pulses ($\nu = 0$). For pulse sequences the power dissipation has to be reduced in accordance with the diagram "permissible pulse load".

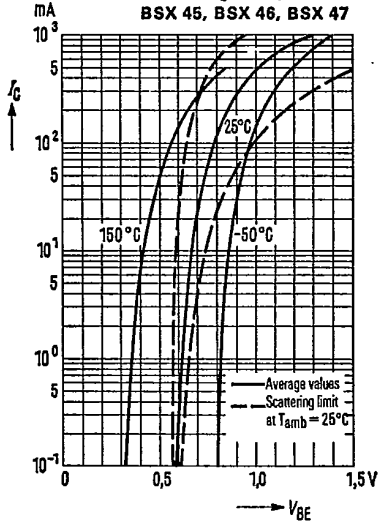
Permissible operating range
 $I_C = f(V_{CE})$; ($T_{case} = 80^\circ C$)



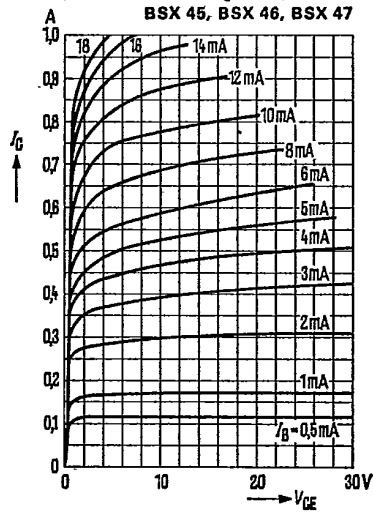
Permissible operating range
 $I_C = f(V_{CE})$; ($T_{case} = 125^\circ C$)



Collector current $I_C = f(V_{BE})$
 $V_{CE} = 1V$; $T_{amb} = \text{parameter}$
 (common emitter configuration)

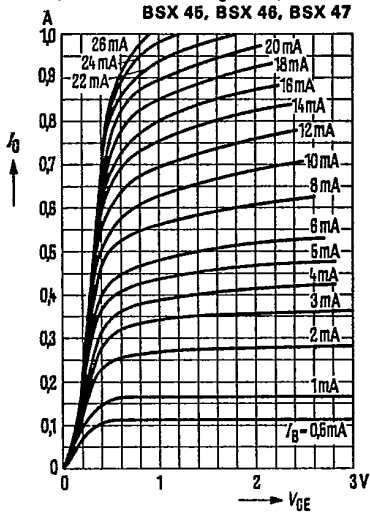


Output characteristics $I_C = f(V_{CE})$
 $I_B = \text{parameter}$
 (common emitter configuration)

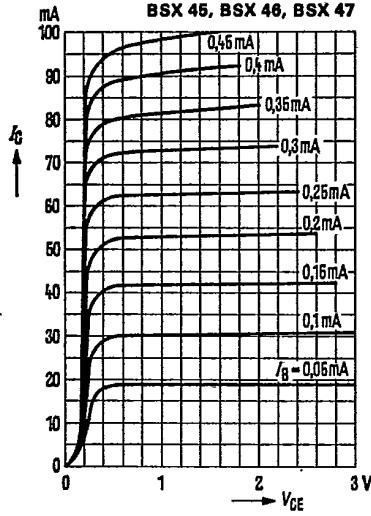


— SIEMENS AKTIENGESELLSCHAFT —

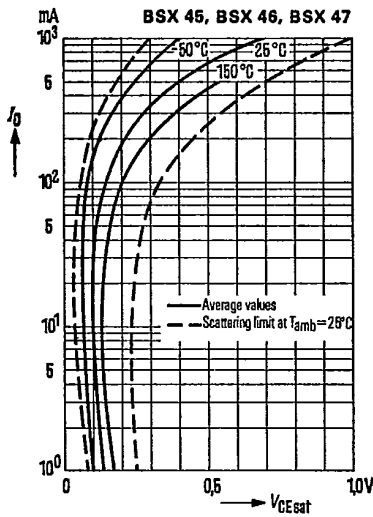
Output characteristics $I_C = f(V_{CE})$
 $I_B = \text{parameter}$
(common emitter configuration)



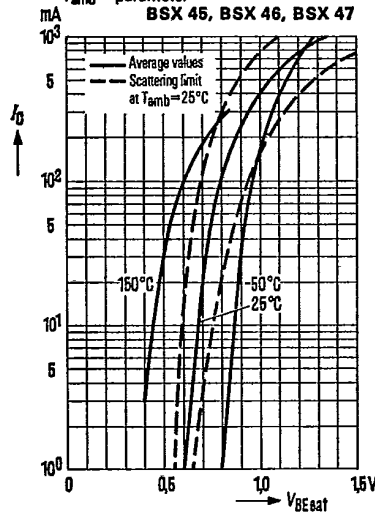
Output characteristics $I_C = f(V_{CE})$
 $I_B = \text{parameter}$
(common emitter configuration)



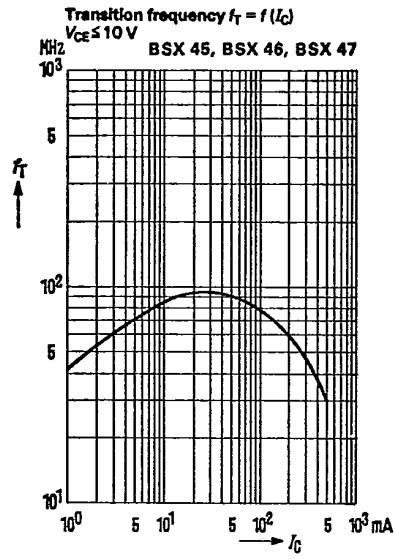
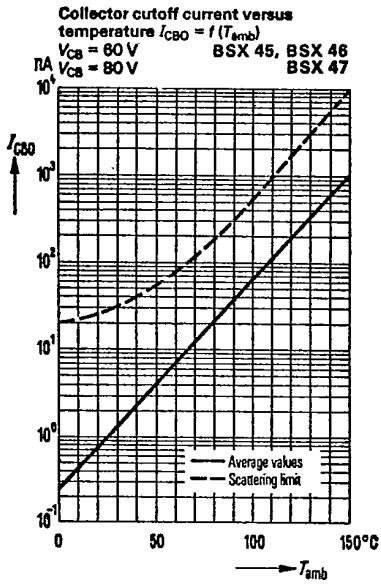
Saturation voltage $V_{CEsat} = f(I_C)$
 $h_{FE} = 10; T_{amb} = \text{parameter}$



Saturation voltage $V_{BEsat} = f(I_C)$
 $h_{FE} = 10; V_{CE} = 1V;$
 $T_{amb} = \text{parameter}$



SIEMENS AKTIENGESELLSCHAFT





LittleDiode supplies new, hard to find or obsolete electronic components and semiconductors all over the world.

With over two million different components listed you are sure to find the part you need.

Feel free to visit us today at our online store:

LittleDiode.com

Looking forward to providing you with the best possible service.